



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

WBFBP-03B Plastic-Encapsulate Transistors

TK3904NND03 TRANSISTOR

DESCRIPTION

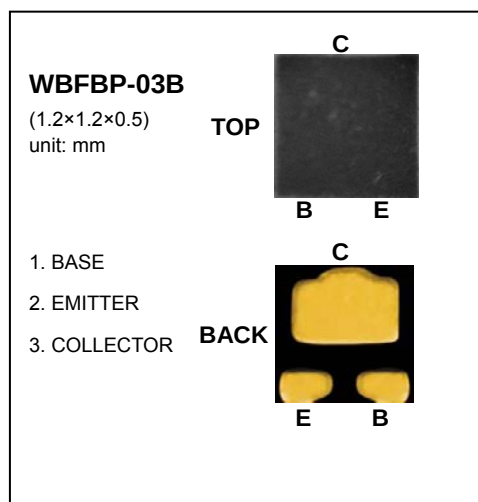
NPN Epitaxial Silicon Transistor

FEATURES

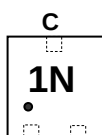
Epitaxial Planar Die Construction
Complementary PNP Type Available (TK3906NND03)
Ultra-Small Surface Mount Package
Also Available in Lead Free Version

APPLICATION

General Purpose Amplifier, switching
For portable equipment:(i.e. Mobile phone,MP3, MD,CD-ROM,
DVD-ROM, Note book PC, etc.)



MARKING:1N



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MAXIMUM RATINGS* $T_A=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	40	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current -Continuous	0.2	A
P_C	Collector Dissipation	0.15	W
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55-150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=10\mu\text{A}, I_E=0$	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}, I_B=0$	40			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10\mu\text{A}, I_C=0$	6			V
Collector cut-off current	I_{CEX}	$V_{CE}=30\text{V}, V_{EB(off)}=3\text{V}$			0.05	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5\text{V}, I_C=0$			0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=1\text{V}, I_C=0.1\text{mA}$	40			
	$h_{FE(2)}$	$V_{CE}=1\text{V}, I_C=1\text{mA}$	70			
	$h_{FE(3)}$	$V_{CE}=1\text{V}, I_C=10\text{mA}$	100		300	
	$h_{FE(4)}$	$V_{CE}=1\text{V}, I_C=50\text{mA}$	60			
	$h_{FE(5)}$	$V_{CE}=1\text{V}, I_C=100\text{mA}$	30			
Collector-emitter saturation voltage	$V_{CE(sat)1}$	$I_C=10\text{mA}, I_B=1\text{mA}$			0.2	V
	$V_{CE(sat)2}$	$I_C=50\text{mA}, I_B=5\text{mA}$			0.3	V
Base-emitter saturation voltage	$V_{BE(sat)1}$	$I_C=10\text{mA}, I_B=1\text{mA}$	0.65		0.85	V
	$V_{BE(sat)2}$	$I_C=50\text{mA}, I_B=5\text{mA}$			0.95	V
Transition frequency	f_T	$V_{CE}=20\text{V}, I_C=10\text{mA}, f=100\text{MHz}$	300			MHz

ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector output capacitance	C_{ob}	$V_{CB}=5V, I_E=0, f=1MHz$			4	pF
Noise figure	NF	$V_{CE}=5V, I_C=0.1mA$,			5	dB
Delay time	t_d	$V_{CC}=3V, V_{BE(off)}=-0.5V,$ $I_C=10mA, I_{B1}=1mA$			35	nS
Rise time	t_r				35	nS
Storage time	t_s	$V_{CC}=3V, I_C=10mA$			200	nS
Fall time	t_f	$I_{B1}=I_{B2}=1mA$			50	nS

Typical Characteristics

TK3904NND03

